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L4: Entry 1 of 1

File: JPAB

Jul 1, 1985

PUB-NO: JP360123074A

DOCUMENT-IDENTIFIER: JP 60123074 A

TITLE: AMORPHOUS SILICON SOLAR CELL

PUBN-DATE: July 1, 1985

INVENTOR-INFORMATION:

NAME

COUNTRY

HAMA, TOSHIO

US-CL-CURRENT: [136/244](#); [136/258](#)

INT-CL (IPC): H01L 31/04

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Draw. Desc	Image
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L4: Entry 1 of 1

File: JPAB

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HAMA, TOSHIO

ASSIGNEE-INFORMATION:

NAME

COUNTRY

FUJI ELECTRIC CORP RES & DEV LTD

N/A

APPL-NO: JP58231798

APPL-DATE: December 8, 1983

US-CL-CURRENT: 136/244; 136/258

INT-CL (IPC): H01L 31/04

ABSTRACT:

PURPOSE: To shorten a manufacturing process for an insulating layer to a metallic substrate for an a-Si solar cell element formed on the substrate, and to reduce manufacturing cost by using an amorphous silicon carbide (a-SiC) layer as the insulating layer.

CONSTITUTION: A plurality of regions of insulating layers 2 consisting of a-SiC are shaped on a metallic substrate 1 while being mutually separated, N type a-Si layers 3 functioning as one electrodes are laminated on a plurality of the regions, I type a-Si layers 4 on regions, in which one parts of the N type layers are removed, and P type a-Si layers 5 on the layers 4 in succession, thus forming active layers 10 for mutually separated solar cell elements. The active layers 10, the outer circumferential surfaces of the insulating layers 2 and the exposed surfaces of the metallic substrate 1 are coated with an insulating film 6 consisting of a substance such as silicon oxide. The solar cell elements adjoining in succession are connected in series by forming transparent electrode layers 7 connecting sections 71 on the surfaces of the P type layers for each solar cell element and sections 72 on the exposed surfaces of the N type layers for adjacent elements. The active layers 10 may be laminated in order of P types, I types and N types from the insulating layers 2 sides.

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